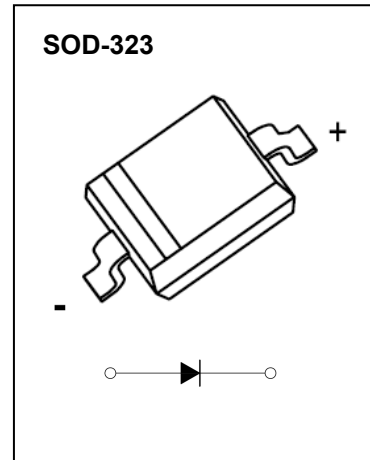
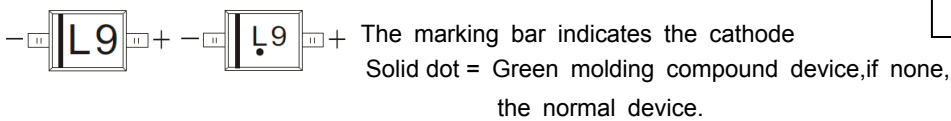


SOD-323 Plastic-Encapsulate Diodes

FEATURES

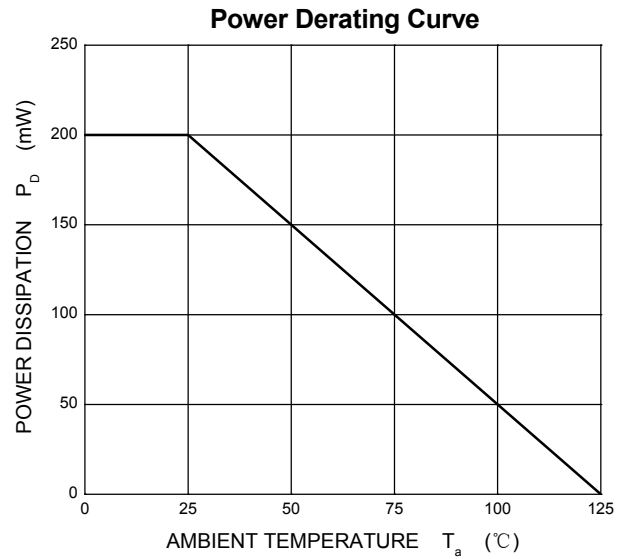
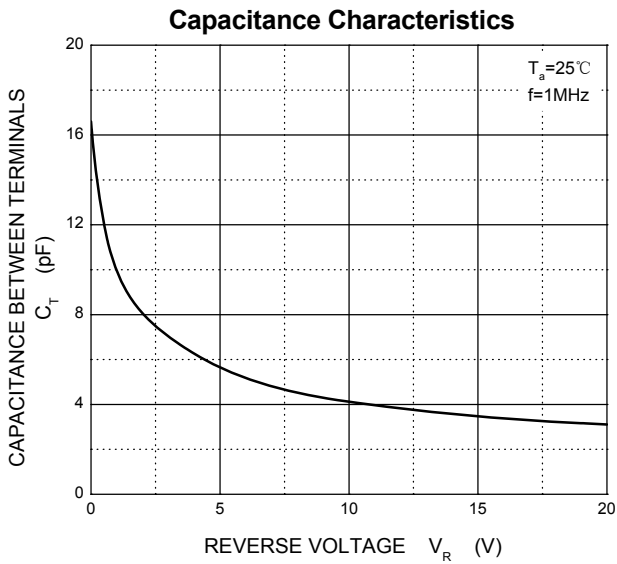
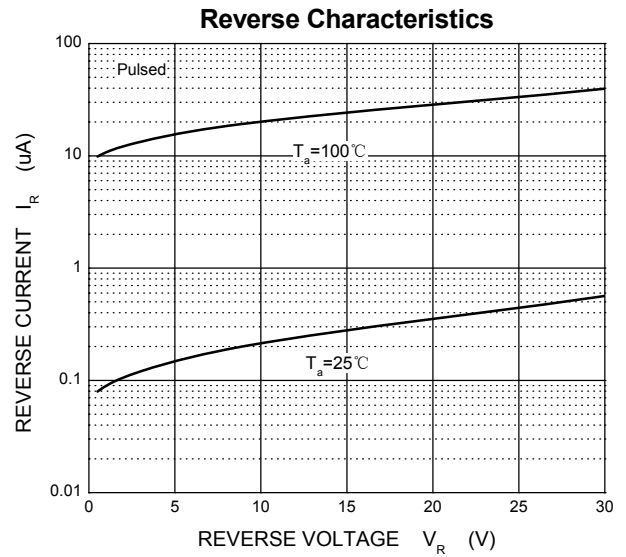
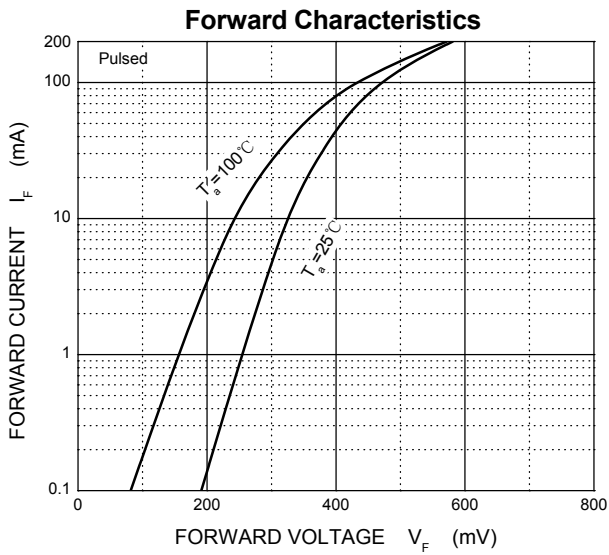
- Extremely Fast Switching Speed
- Low Forward Voltage

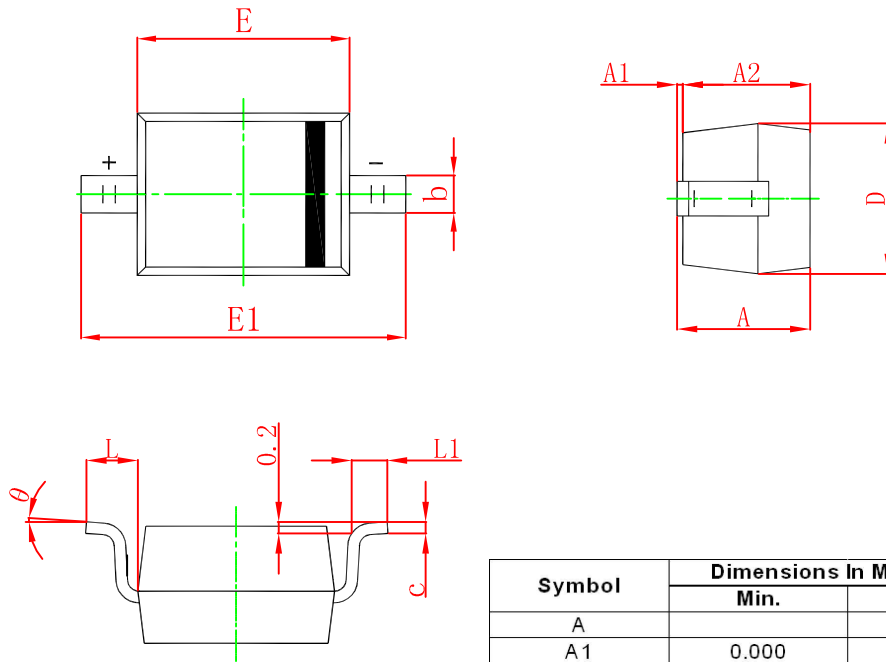
MARKING: L9

Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	30	V
DC Blocking Voltage	V_R	21	V
Average Rectified Output Current	I_O	100	mA
Forward Continuous Current	I_F	200	mA
Repetitive Peak Forward Current	I_{FRM}	300	mA
Non-repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	600	mA
Power Dissipation	P_D	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	500	°C/W
Junction Temperature	T_J	125	°C
Storage Temperature Range	T_{STG}	-55~+150	°C

Electrical Characteristics @Ta=25°C

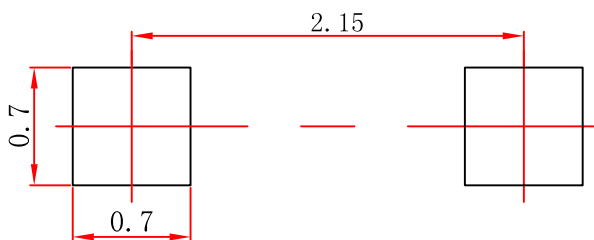
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	30			V
Forward voltage	V_{F1}	$I_F=0.1mA$			240	mV
	V_{F2}	$I_F=1.0mA$			320	mV
	V_{F3}	$I_F=10mA$			400	mV
	V_{F4}	$I_F=30mA$			500	mV
	V_{F5}	$I_F=100mA$			1000	mV
Reverse current	I_R	$V_R=25V$			2.0	uA
Reverse recovery time	t_{rr}	$I_F=10mA, I_R=10mA$ to 1mA , $R_L=100\Omega$			5.0	ns
Capacitance between terminals	C_T	$V_R=1V, f=1MHz$			10	pF





Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A		1.000		0.039
A1	0.000	0.100	0.000	0.004
A2	0.800	0.900	0.031	0.035
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	1.200	1.400	0.047	0.055
E	1.600	1.800	0.063	0.071
E1	2.550	2.750	0.100	0.108
L	0.475 REF.		0.019 REF.	
L1	0.250	0.400	0.010	0.016
θ	0°	8°	0°	8°

SOD-323 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.